

Transistors

PNP General Purpose Transistor

BC858BW / BC858B

●Features

- 1) $BV_{CEO} < -30V$ ($I_C = -1mA$)
- 2) Complements the BC848B / BC848BW.

●Package, marking and packaging specifications

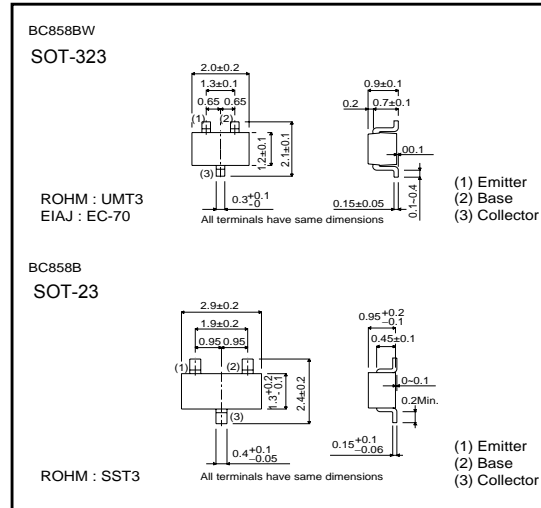
| Part No. | BC858BW | BC858B |
|------------------------------|---------|--------|
| Packaging type | UMT3 | SST3 |
| Marking | G3K | G3K |
| Code | T106 | T116 |
| Basic ordering unit (pieces) | 3000 | 3000 |

●Absolute maximum ratings ($T_a = 25^\circ C$)

| Parameter | Symbol | Limits | Unit |
|-----------------------------|-----------|-------------|------------|
| Collector-base voltage | V_{CBO} | -30 | V |
| Collector-emitter voltage | V_{CEO} | -30 | V |
| Emitter-base voltage | V_{EBO} | -5 | V |
| Collector current | I_C | -0.1 | A |
| Collector power dissipation | P_C | 0.2 | W * |
| | | 0.35 | |
| Junction temperature | T_J | 150 | $^\circ C$ |
| Storage temperature | T_{stg} | -65 to +150 | $^\circ C$ |

* When mounted on $7 \times 5 \times 0.6$ mm ceramic board.

●External dimensions (Unit : mm)



●Electrical characteristics ($T_a = 25^\circ C$)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|--------------------------------------|---------------|------|------|-------|---------|--|
| Collector-base breakdown voltage | BV_{CBO} | -30 | - | - | V | $I_C = -50\mu A$ |
| Collector-emitter breakdown voltage | BV_{CEO} | -30 | - | - | V | $I_C = -1mA$ |
| Emitter-base breakdown voltage | BV_{EBO} | -5 | - | - | V | $I_E = -50\mu A$ |
| Collector cutoff current | I_{CBO} | - | - | -100 | nA | $V_{CB} = -30V$ |
| | | - | - | 4 | μA | $V_{CB} = -30V, T_a = 150^\circ C$ |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | - | - | -0.3 | V | $I_C/I_B = -10mA/-0.5mA$ |
| | | - | - | -0.65 | V | $I_C/I_B = -100mA/-5mA$ |
| Base-emitter saturation voltage | $V_{BE(on)}$ | -0.6 | - | -0.75 | V | $V_{CE}/I_C = -5V/-10mA$ |
| DC current transfer ratio | h_{FE} | 210 | - | 480 | - | $V_{CE}/I_C = -5V/-2mA$ |
| Transition frequency | f_T | - | 250 | - | MHz | $V_{CE} = -5V, I_E = 20mA, f = 100MHz$ |
| Output capacitance | C_{ob} | - | 4.5 | - | pF | $V_{CB} = -10V, I_E = 0, f = 1MHz$ |

●Electrical characteristics curves

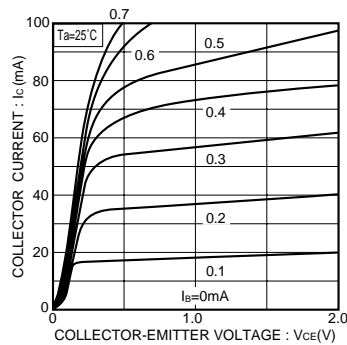


Fig.1 Grounded emitter output characteristics (I)

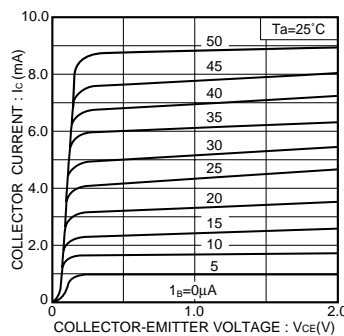


Fig.2 Grounded emitter output characteristics (II)

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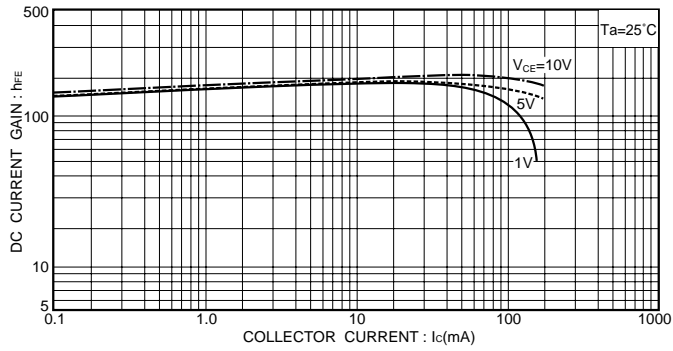


Fig.3 DC current gain vs. collector current (I)

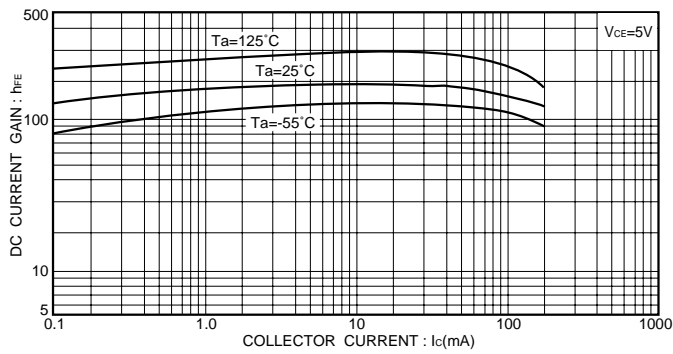


Fig.4 DC current gain vs. collector current (II)

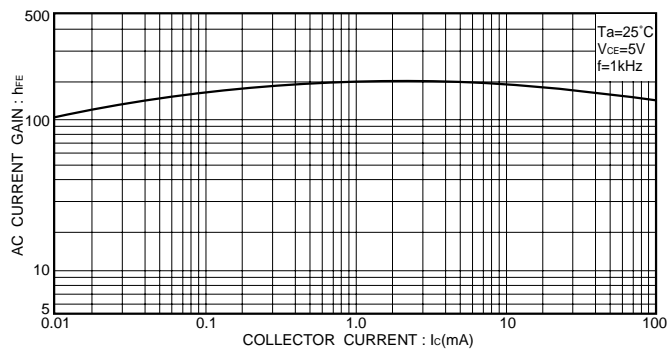


Fig.5 AC current gain vs. collector current

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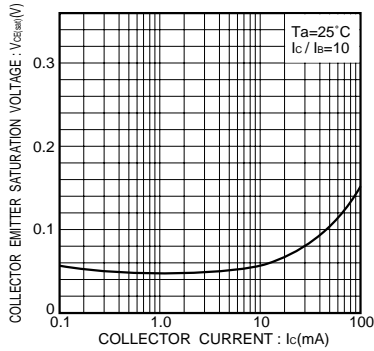


Fig.6 Collector-emitter saturation voltage vs. collector current

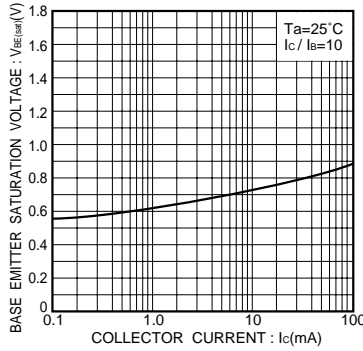


Fig.7 Base-emitter saturation voltage vs. collector current

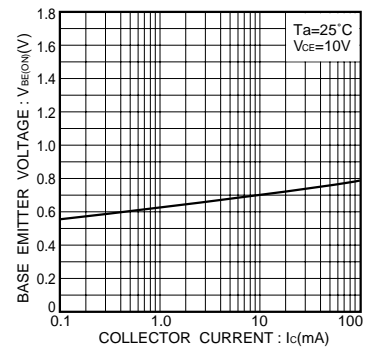


Fig.8 Grounded emitter propagation characteristics

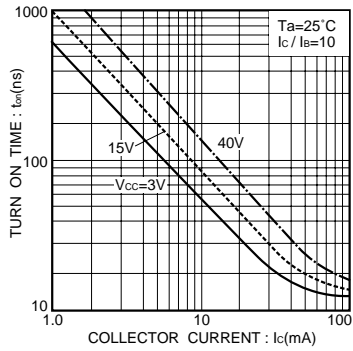


Fig.9 Turn-on time vs. collector current

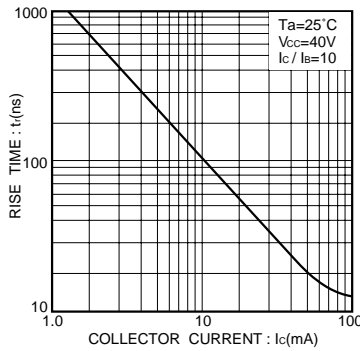


Fig.10 Rise time vs. collector current

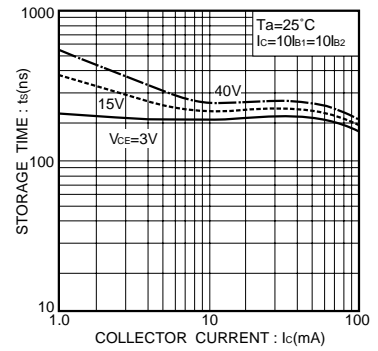


Fig.11 Storage time vs. collector current

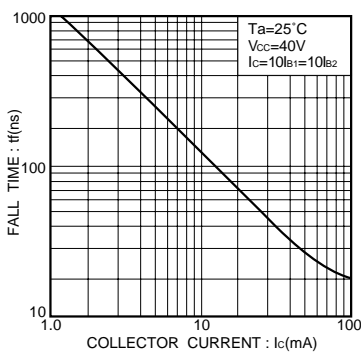


Fig.12 Fall time vs. collector current

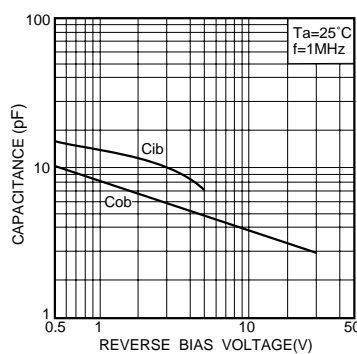


Fig.13 Input/output capacitance vs. voltage

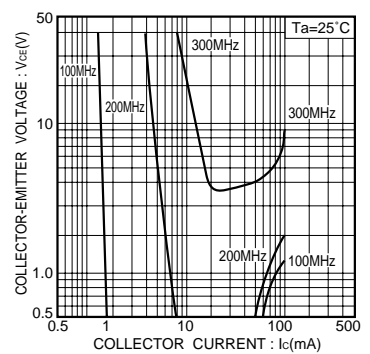


Fig.14 Gain bandwidth product

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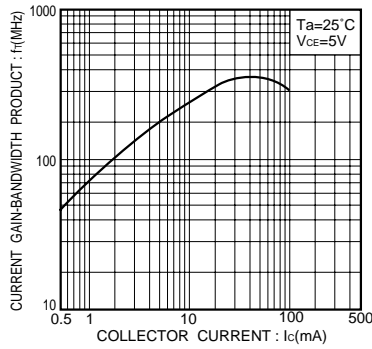


Fig.15 Gain bandwidth product vs. collector current

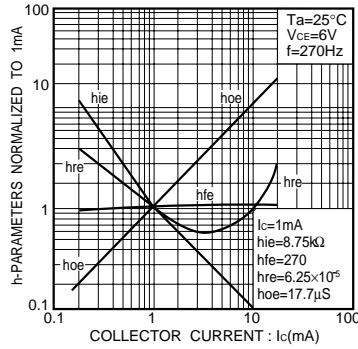


Fig.16 h parameter vs. collector current

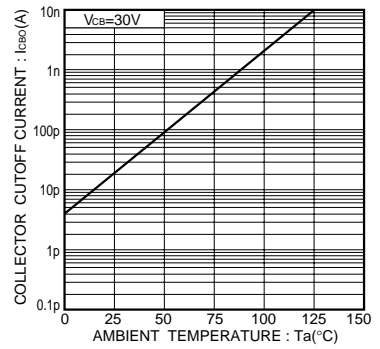


Fig.17 Noise characteristics (I)

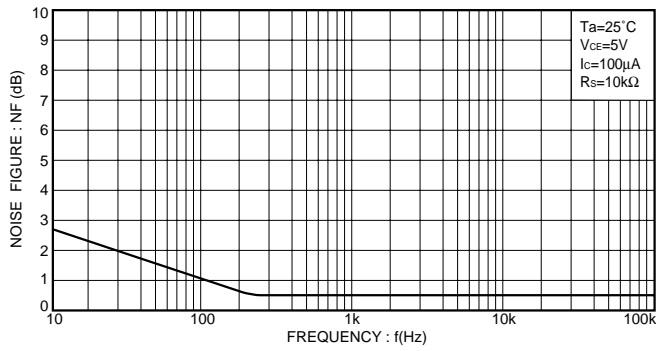


Fig.18 Noise vs. collector current

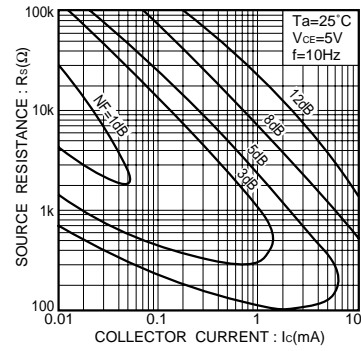


Fig.19 Noise characteristics (II)

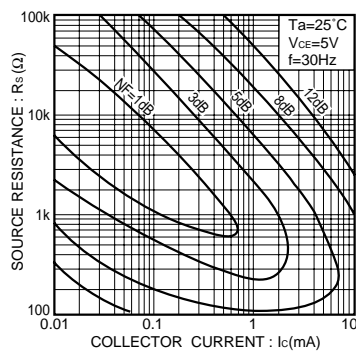


Fig.20 Noise characteristics (III)

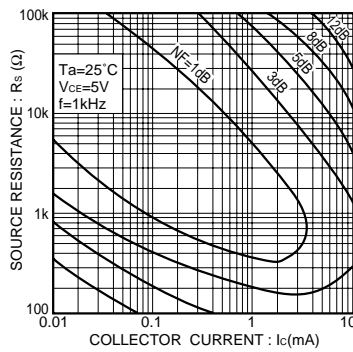


Fig.21 Noise characteristics (IV)

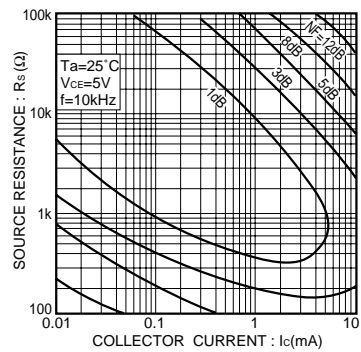


Fig.22 Noise characteristics (V)

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